

SEMiX453GB176HDs



SEMiX® 3s

Trench IGBT Modules

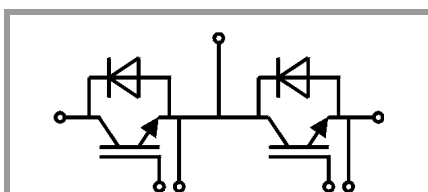
SEMiX453GB176HDs

Features

- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- UL recognised file no. E63532

Typical Applications*

- AC inverter drives
- UPS
- Electronic welders



GB

Absolute Maximum Ratings				
Symbol	Conditions		Values	Unit
IGBT				
V _{CES}	T _j = 25 °C		1700	V
I _C	T _j = 150 °C	T _c = 25 °C	444	A
		T _c = 80 °C	315	A
I _{Cnom}			300	A
I _{CRM}	I _{CRM} = 2xI _{Cnom}		600	A
V _{GES}			-20 ... 20	V
t _{psc}	V _{CC} = 1000 V V _{GE} ≤ 20 V V _{CES} ≤ 1700 V	T _j = 125 °C	10	µs
T _j			-55 ... 150	°C
Inverse diode				
I _F	T _j = 150 °C	T _c = 25 °C	545	A
		T _c = 80 °C	365	A
I _{Fnom}			300	A
I _{FRM}	I _{FRM} = 2xI _{Fnom}		600	A
I _{FSM}	t _p = 10 ms, sin 180°, T _j = 25 °C		2900	A
T _j			-40 ... 150	°C
Module				
I _{t(RMS)}	T _{terminal} = 80 °C		600	A
T _{stg}			-40 ... 125	°C
V _{isol}	AC sinus 50Hz, t = 1 min		4000	V

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
IGBT						
V _{CE(sat)}	I _C = 300 A V _{GE} = 15 V chiplevel	T _j = 25 °C		2	2.45	V
		T _j = 125 °C		2.5	2.9	V
V _{CE0}		T _j = 25 °C		1	1.2	V
		T _j = 125 °C		0.9	1.1	V
r _{CE}	V _{GE} = 15 V	T _j = 25 °C		3.3	4.2	mΩ
		T _j = 125 °C		5.2	6.0	mΩ
V _{GE(th)}	V _{GE} =V _{CE} , I _C = 12 mA		5.2	5.8	6.4	V
I _{CES}	V _{GE} = 0 V	T _j = 25 °C			3	mA
	V _{CE} = 1700 V	T _j = 125 °C				mA
C _{ies}	V _{CE} = 25 V V _{GE} = 0 V	f = 1 MHz		26.4		nF
C _{oes}		f = 1 MHz		1.10		nF
C _{res}		f = 1 MHz		0.88		nF
Q _G	V _{GE} = - 8 V...+ 15 V			2799		nC
R _{Gint}	T _j = 25 °C			2.50		Ω
t _{d(on)}	V _{CC} = 1200 V	T _j = 125 °C		335		ns
t _r	I _C = 300 A	T _j = 125 °C		70		ns
E _{on}	V _{GE} = ±15 V	T _j = 125 °C		215		mJ
t _{d(off)}	R _{G on} = 4.3 Ω	T _j = 125 °C		990		ns
t _f	R _{G off} = 4.3 Ω	T _j = 125 °C		150		ns
E _{off}		T _j = 125 °C		125		mJ
R _{th(j-c)}	per IGBT				0.071	K/W

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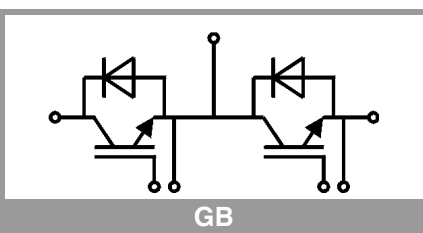
Features

- Homogeneous Si
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- $V_{CE(sat)}$ with positive temperature coefficient
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Typical Applications*

- AC inverter drives
- UPS
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Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Inverse diode						
V _F = V _{EC}	I _F = 300 A	T _j = 25 °C		1.5	1.70	V
	V _{GE} = 0 V chip	T _j = 125 °C		1.4	1.6	V
V _{F0}		T _j = 25 °C	0.9	1.1	1.3	V
		T _j = 125 °C	0.7	0.9	1.1	V
r _F		T _j = 25 °C	1.3	1.3	1.3	mΩ
		T _j = 125 °C	1.8	1.8	1.8	mΩ
I _{RRM}	I _F = 300 A	T _j = 125 °C	350			A
Q _{rr}	di/dt _{off} = 4700 A/μs	T _j = 125 °C	115			μC
E _{rr}	V _{GE} = -15 V	T _j = 125 °C	65			mJ
R _{th(j-c)}	V _{CC} = 1200 V per diode				0.11	K/W
Module						
L _{CE}			20			nH
R _{CC'+EE'}	res., terminal-chip	T _C = 25 °C	0.7			mΩ
		T _C = 125 °C	1			mΩ
R _{th(c-s)}	per module		0.04			K/W
M _s	to heat sink (M5)		3		5	Nm
M _t		to terminals (M6)	2.5		5	Nm
						Nm
w			300			g
Temperatur Sensor						
R ₁₀₀	T _c =100°C (R ₂₅ =5 kΩ)		493 ± 5%			Ω
B _{100/125}	R(Τ)=R ₁₀₀ exp[B _{100/125} (1/T-1/T ₁₀₀)]; T[K];		3550 ±2%			K



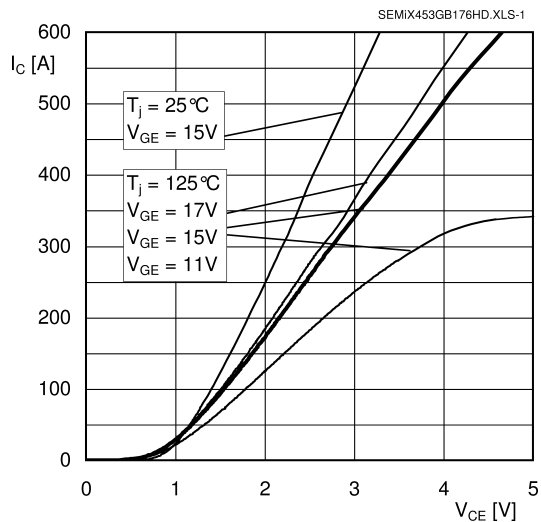


Fig. 1: Typ. output characteristic, inclusive $R_{CC'+EE'}$

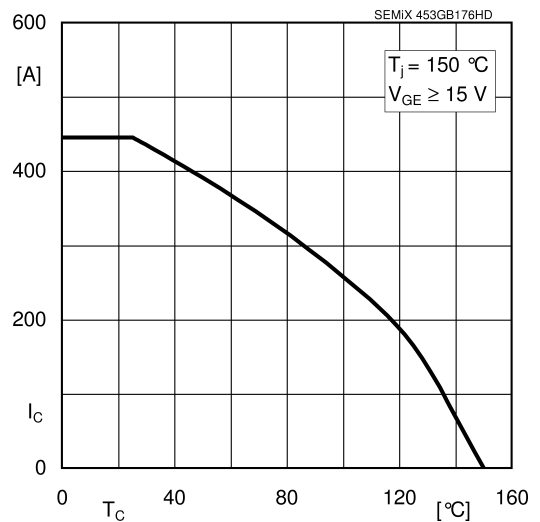


Fig. 2: Rated current vs. temperature $I_C = f(T_C)$

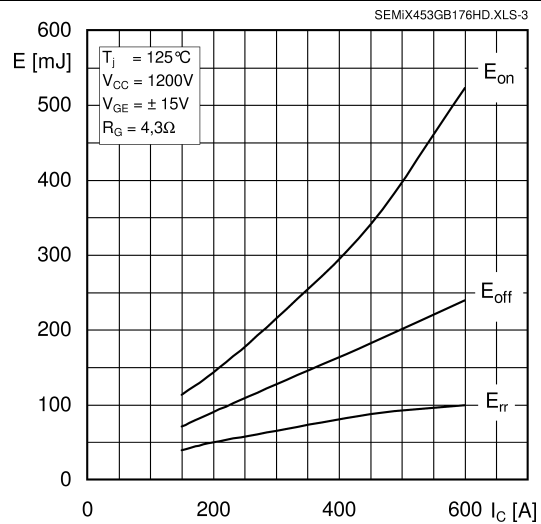


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

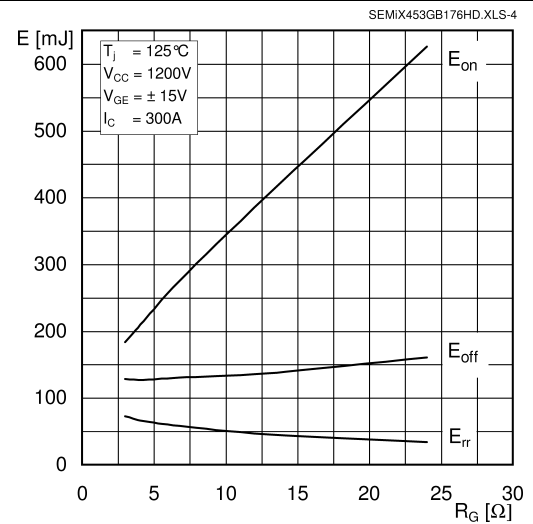


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

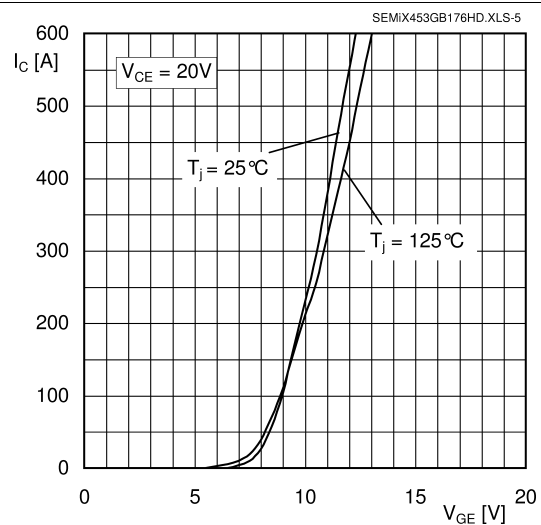


Fig. 5: Typ. transfer characteristic

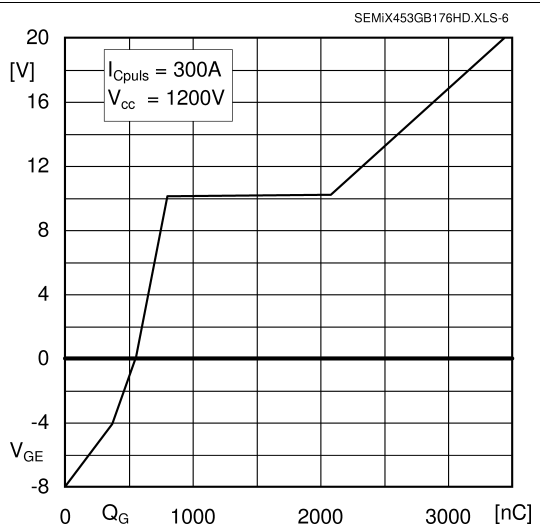
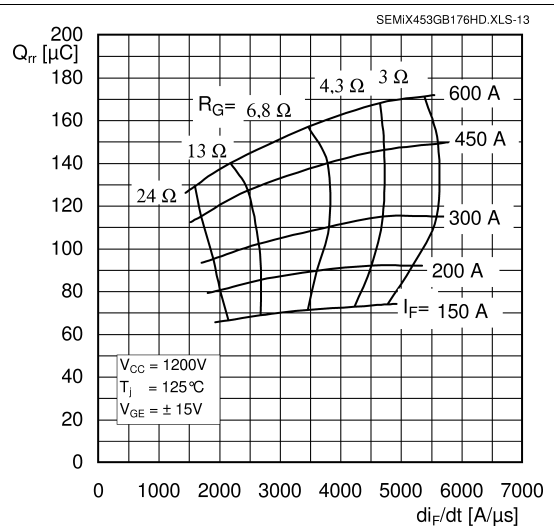
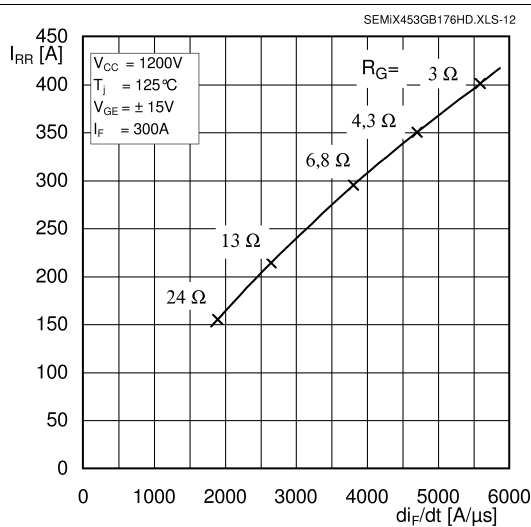
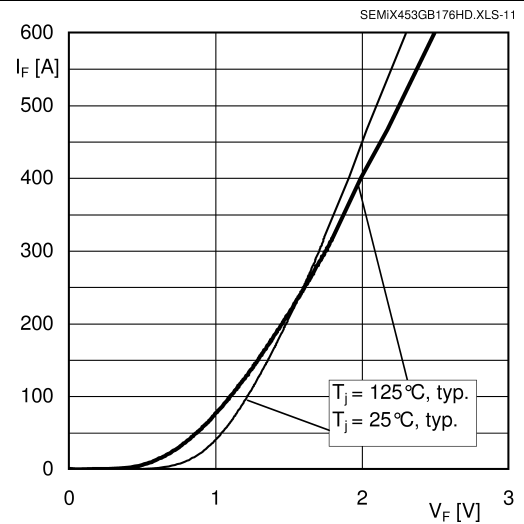
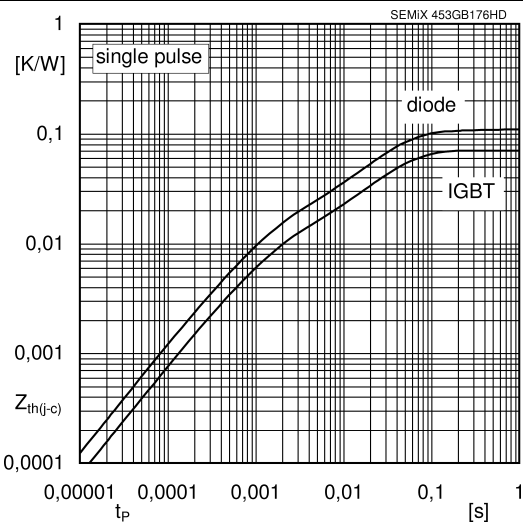
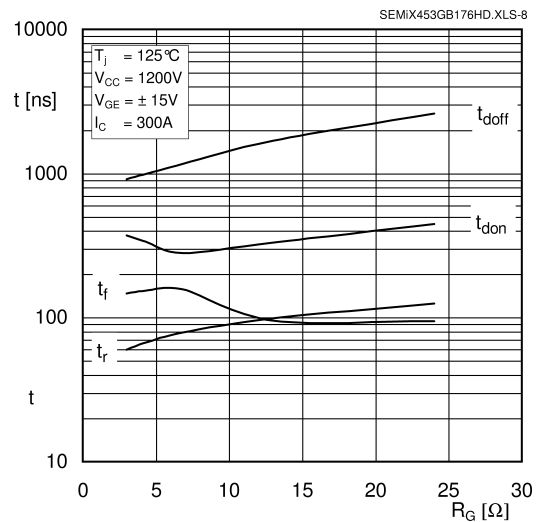
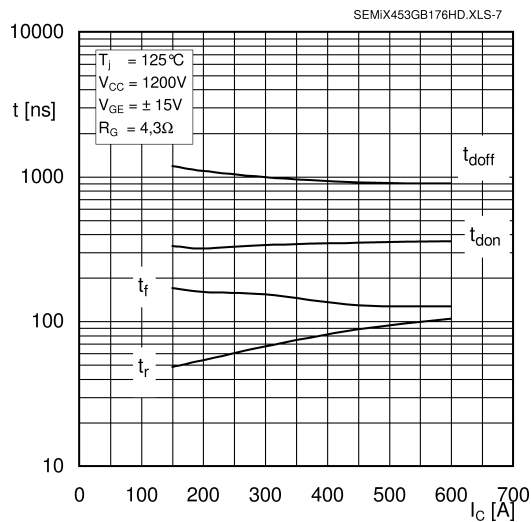
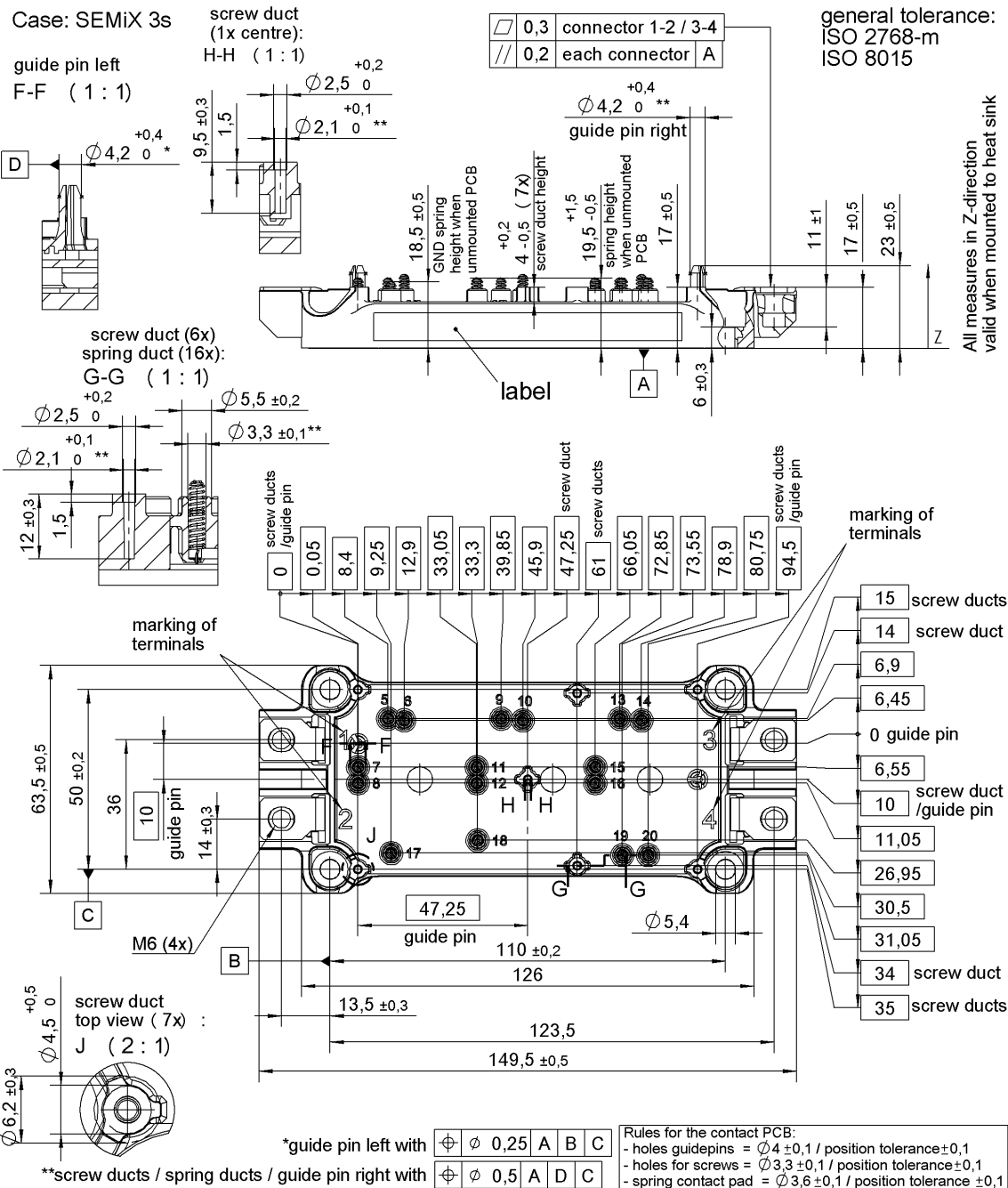


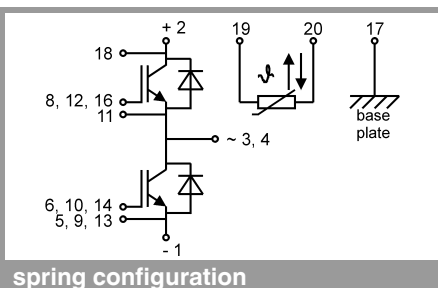
Fig. 6: Typ. gate charge characteristic



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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our staff.